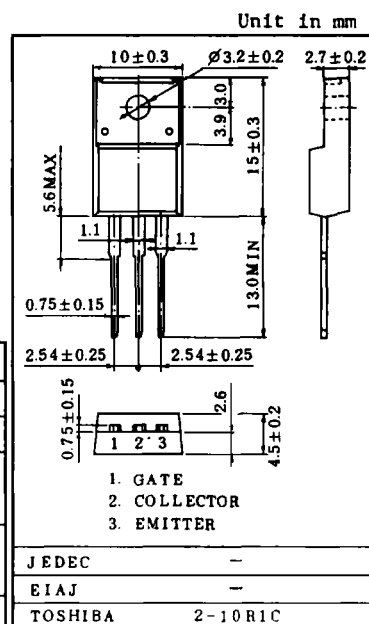


STROBE FLASH APPLICATIONS

- High Input Impedance
- Low Saturation Voltage : $V_{CE(sat)} = 8V(\text{Max.})(I_C=130A)$
- Enhancement-Mode
- 12V Gate Drive

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	V_{CES}	400	V
Gate-Emitter Voltage	V_{GES}	± 20	V
Collector Current	DC	I_C	A
	1ms	I_{CP}	
Collector Power Dissipation	$T_a=25^\circ\text{C}$	P_C	W
	$T_c=25^\circ\text{C}$	P_C	
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55\sim 150$	$^\circ\text{C}$
Screw Torque	-	0.6	N·m



Weight : 1.7g

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GES}	$V_{GE}=\pm 20V, V_{CE}=0$	-	-	± 100	nA
Collector Cut-off Current	I_{CES}	$V_{CE}=400V, V_{GE}=0$	-	-	10	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C=2mA, V_{GE}=0$	400	-	-	V
Gate-Emitter Cut-off Voltage	$V_{GE(OFF)}$	$I_C=1mA, V_{CE}=5V$	2	-	5	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=130A, V_{GE}=12V(\text{Pulsed})$	-	5	8	V
Input Capacitance	C_{ies}	$V_{CE}=10V, V_{GE}=0, f=1MHz$	-	1850	-	pF
Switching Time	Rise Time		-	0.1	0.5	μs
	Turn-on Time		-	0.15	0.5	
	Fall Time		-	4.0	6.0	
	Turn-off Time		-	4.5	7.0	
Thermal Resistance	$R_{th(j-c)}$	-	-	-	4.16	$^\circ\text{C/W}$

